

# Structure analysis and multiferroic properties of $\text{Zr}^{4+}$ doped $\text{BiFeO}_3$ ceramics

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## Abstract

$\text{Zr}^{4+}$  doped multiferroic ceramics samples  $\text{BiFe}_{1-x}\text{Zr}_x\text{O}_3$  ( $x=0, 0.02, 0.04, 0.06, 0.08, 0.10$ ) were prepared by a solid state reaction method and characterized by X-ray diffraction and X-ray Absorption Fine Structure analysis. X-ray diffraction analysis showed that the characteristic peaks of samples were shifted toward a lower angle with the increase of  $\text{Zr}^{4+}$  doping concentration. It indicated that the doped  $\text{Zr}^{4+}$  ions entered into the crystal lattice. The length of  $\text{Zr-O}$  bond was calculated based on the results of X-ray Absorption Fine Structure analysis. The abnormal dielectric constant near the Neel temperature of  $\text{BiFe}_{1-x}\text{Zr}_x\text{O}_3$  indirectly demonstrated the coupling between magnetic and electric properties of  $\text{BiFe}_{1-x}\text{Zr}_x\text{O}_3$ . The Neel temperature of  $\text{Zr}^{4+}$  doped  $\text{BiFeO}_3$  was  $\sim 20^\circ\text{C}$  lower than that of the undoped  $\text{BiFeO}_3$ . The Neel temperature of  $\text{BiFe}_{1-x}\text{Zr}_x\text{O}_3$  will be different if the doping amount of  $\text{Zr}^{4+}$  is different. However, all the prepared samples are antiferromagnetic.

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## 1. Introduction

Multiferroic materials have attracted great attention because of two reasons. One is the potential applications in multifunctional sensors, convertors and microelectronic devices [1,2]. The other is their interesting physical problems, for example, the coupling between magnetic order parameters and electric order parameters [3,4]. As other important multiferroic materials,  $\text{BiFeO}_3$  possesses ferroelectricity, anti-ferromagnetism and ferroelasticity [5]. Furthermore,  $\text{BiFeO}_3$  is the only single-phase multiferroics, which has both Curie temperature ( $T_C$ , 1103 K) and Neel temperature ( $T_N$ , transition temperature from anti-ferromagnetism to para-magnetism, 643 K) above room temperature [6]. It is a good candidate for making lead-free ferroelectric memory devices due to its large spontaneous polarization ( $P_S$ , 88–100  $\mu\text{C}/\text{cm}^2$ ) [5] and high  $T_C$  [7,8]. However, its main drawback, the relatively high leakage current, impedes its further applications. The leakage current is caused by oxygen vacancies and  $\text{Fe}^{2+}$  in  $\text{BiFeO}_3$ . Oxygen vacancies come from the evaporation of Bi, and  $\text{Fe}^{2+}$  comes from the reduction of  $\text{Fe}^{3+}$  [9].

Although the impurity phases are inevitable in  $\text{BiFeO}_3$  ceramic materials prepared by the solid state reaction method [6], it has been demonstrated that there is no correlation between the impurity phase intensity in XRD patterns and the leakage current [10–12]. Many methods have been tried to decrease the leakage current of  $\text{BiFeO}_3$ , such as aliovalent-ion-doping [9], rapid liquid phase sintering [12], thin film, etc. [7,13,14]. As for  $\text{BiFeO}_3$  ceramics samples prepared by the solid state reaction method, doping is a main and convenient approach to decrease the leakage current. Decrease in the leakage current of  $\text{Zr}^{4+}$  doped  $\text{BiFeO}_3$  prepared by the solid state reaction method was reported previously and the enhanced properties could be attributed to the change in the conduction mechanism and the competition of two different charge-compensation ways [15]. In this paper, the further discussions on  $\text{Zr}^{4+}$  doped  $\text{BiFeO}_3$  prepared by the solid state reaction method will be carried out, such as the differences between  $\text{Fe-O}$  and  $\text{Zr-O}$  bond, and the resultant effect on the dielectric and magnetic properties.

## 2. Experiments

$\text{BiFe}_{1-x}\text{Zr}_x\text{O}_3$  (BFZO,  $x=0, 0.02, 0.04, 0.06, 0.08, 0.10$ ) samples were prepared by a solid state reaction method.

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The analytical purity reagents of  $\text{Bi}_2\text{O}_3$ ,  $\text{Fe}_2\text{O}_3$  and  $\text{ZrO}_2$  were mixed in a stoichiometric ratio with 3% (mol) extra  $\text{Bi}_2\text{O}_3$  considering its evaporation. The mixture was milled for 24 h and then calcined in the air at 600 °C for 2 h. Then the calcined powder was milled again and pressed into pellets with 15 mm diameter and 2 mm thickness at the pressure of 135 MPa. The pressed pellets were sintered at 820 °C in the air for 50 min in an alumina crucible. After sintering, the samples with the crucible were immediately taken out from the furnace.

X-ray diffraction (D8 Advance) with  $\text{CuK}\alpha_1$  was used to analyze the phase of BFZO. X-Ray Absorption Fine Structure (XAFS) analysis was carried out with BL14W1 beam line in Shanghai Synchrotron Radiation Facility (SSRF). Ifeffit software was used for XAFS data processing. For the electric properties measurement, the as-sintered BFZO pellets were well polished as thin as 1 mm, and silver paste was pasted on the both sides as the electrodes. Agilent 4284A Precision LCR Meter was used to measure the dielectric properties. Magnetic properties were measured by vibrating sample magnetometer (VSM, Quantum Design).

### 3. Results and discussions

Fig. 1 (a) shows the XRD patterns of BFZO samples. All the XRD patterns indicate that it is a typical rhombohedral structure. There are two kinds of impurities in the BFZO samples, which are  $\text{Bi}_2\text{Fe}_4\text{O}_9$  and  $\text{Bi}_{25}\text{FeO}_{40}$ , according to the XRD results. The impurities are due to the decomposition of  $\text{BiFeO}_3$  at 720–1040 K during the cooling process from the sintering temperature [6]. As a result, the impurities are inevitable in  $\text{BiFeO}_3$  prepared by the solid state reaction method. Although there are a few impurity phase ( $\leq 10\%$ ) showed in the patterns, the electrical properties of samples would not be affected [10–12]. It is found that the typical diffraction peaks are shifted toward a lower angle in Fig. 1(b) and (c). It means that  $\text{Zr}^{4+}$  ions are entered into the crystal lattice. Because the radius of  $\text{Zr}^{4+}$  ion (0.72 Å) is larger than that of  $\text{Fe}^{3+}$

ion (0.65 Å)[16], the unit cell size of BFO would be distorted and enlarged when  $\text{Zr}^{4+}$  entered into the lattice. As a result, the diffraction peaks of BFZO samples in XRD patterns would be shifted toward a lower angle. For further analysis, the neighbor coordinate conditions of  $\text{Zr}^{4+}$  ions in BFZO will be investigated by XAFS.

Fig. 2 shows the variation of Fourier transformed XAFS spectra of Zr K edge vs. the neighbor interatomic distance. Due to the time limitation of XAFS experiment, the sample of  $x=0.02$  is not tested. The corresponding original data of X-ray absorption spectroscopies of K edge of  $\text{Zr}^{4+}$  ions are depicted in the inset of Fig. 2.

The original XAFS data are processed with Ifeffit software (free download, <http://cars9.uchicago.edu/ifeffit/>) based on the following theory reported by Stern, Sayer, and Lytle in 1975.[17,18]

The origin XAFS data is the relationship between  $\mu(E)$  and  $E$ ,

$$\mu(E) \sim E \quad (1)$$

$\mu(E)$ : absorption coefficient.

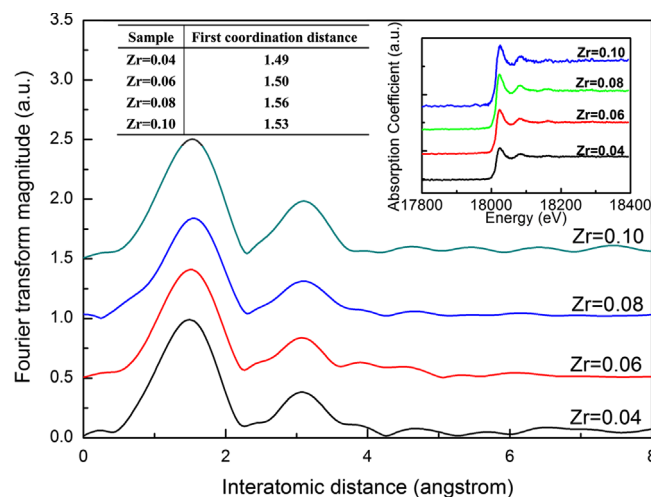


Fig. 2. Fourier transformed XAFS spectrum of Zr K edge.

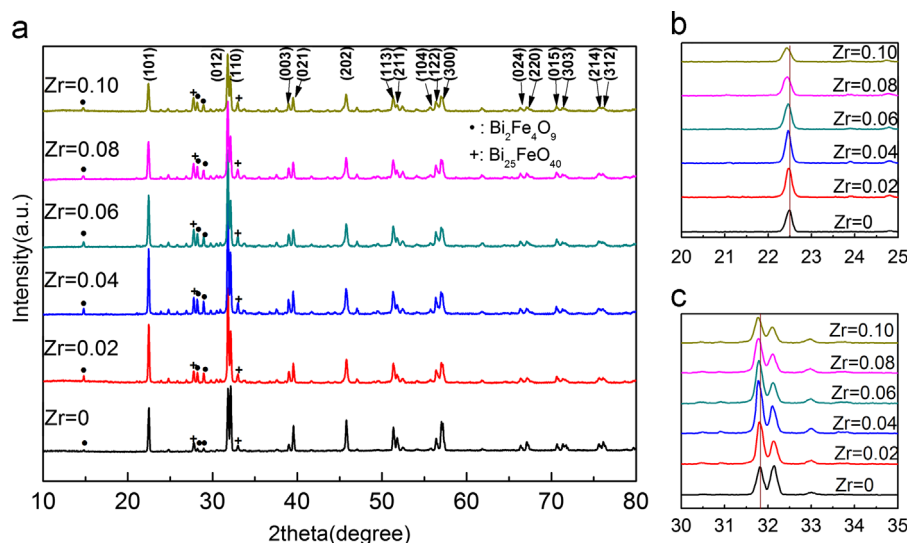


Fig. 1. The XRD patterns of BFZO.

Absorption coefficient must be nominalized and intrinsic absorption must be deducted, as following:

$$\chi(E) = \frac{\mu(E) - \mu_0(E)}{\mu_0(E)} \quad (2)$$

$\chi(E)$ : nominalized absorption coefficient,  $\mu_0(E)$ : pre-edge baseline of absorption coefficient spectrum.

In the further analysis, the independent variables in Eq. (2) must be transformed from  $R$  space to  $k$  space, the relationship between  $R$  and  $k$  as following:

$$k = \frac{2\pi}{\lambda} = \sqrt{\frac{2m}{\hbar}}(E - E_0) \quad (3)$$

Because of the dumping of amplitude, the  $\chi(E)$  must be multiplied by a weighting factor  $k^n$ , as for Zr,  $n=2$ . And then, the absorption coefficient Eq. (2) becomes

$$k^2 \chi(k) \sim k \quad (4)$$

And then, the Eq. (4) can be transformed from  $k$  space to  $R$  space by Fourier transform; the transform equation is listed below:

$$\rho(R) = \frac{1}{\sqrt{2\pi}} \int_{k_{\min}}^{k_{\max}} \omega(k) k^2 \chi e^{-2ikR} dk \quad (5)$$

$$\omega(k) = \begin{cases} 0 & k < k_{\min} \\ \sin^2 \left[ \frac{\pi(k - k_{\min})}{2(k_2 - k_{\min})} \right] & k_{\min} < k < k_2 \\ 1 & k_2 < k < k_3 \\ \cos^2 \left[ \frac{\pi(k - k_3)}{2(k_{\max} - k_3)} \right] & k_3 < k < k_{\max} \\ 0 & k > k_{\max} \end{cases} \quad (6)$$

As for  $Zr^{4+}$  in BFZO,  $k_2=2$ ,  $k_3=10$ .

At last, the absorption coefficient equation is transformed as following:

$$\rho(R) \sim R$$

$R$  is the distance between central absorption atom and the coordinated atoms.

The first coordination peak can be observed clearly in Fig. 2. It corresponds to the nearest oxygen atoms around  $Zr^{4+}$  ion. There are two types of oxygen atoms coordinated to  $Fe^{3+}$  ions in pure  $BiFeO_3$  and the bond lengths are 1.94 Å and 2.13 Å respectively. [19] However, this difference cannot be observed in BFZO. The inset table in Fig. 2 shows the length of Zr–O bond in BFZO. According to Coulomb's law, the bond length  $r \propto Z_1 Z_2 / E_{\text{bond}}$ , where  $Z_1$ ,  $Z_2$  are the valence of ions, and  $E_{\text{bond}}$  is the corresponding bond energy. For the Fe–O bond, the bond energy  $E_{\text{bond}} = 409$  kJ/mol [16],  $Z_1=3$ , and  $Z_2=2$ , so  $Z_1 Z_2 / E_{\text{bond}} = 0.0147$  (kJ/mol) $^{-1}$ . For the Zr–O bond, the bond energy  $E_{\text{bond}} = 760$  kJ/mol [16],  $Z_1=4$  and  $Z_2=2$ , so  $Z_1 Z_2 / E_{\text{bond}} = 0.0105$  (kJ/mol) $^{-1}$ . As a result, the length of Zr–O bond is much shorter than that of Fe–O bond.

Fig. 3 shows the  $\epsilon-T$  (dielectric constant–temperature) spectra of BFZO samples at 100 Hz. There is an abnormality in the spectra between 310 °C and 350 °C, which is corresponding to the transition from anti-ferromagnetism to para-magnetism at the

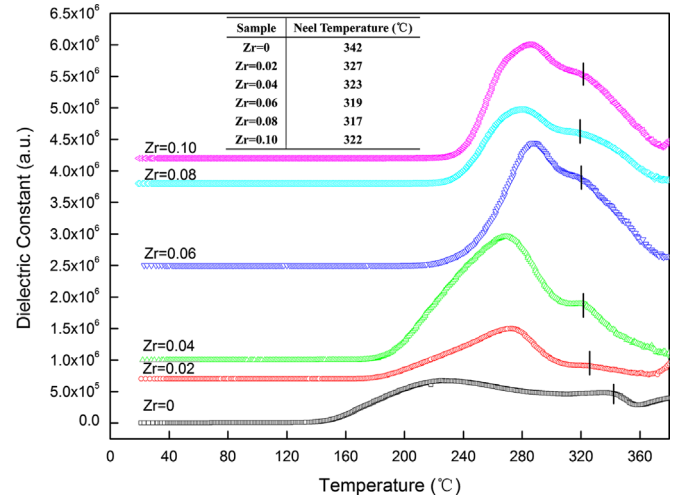


Fig. 3. The  $\epsilon-T$  spectrum of BFZO at 100 Hz.

temperature  $T_N$ . The existence of impurity phases in BFZO results in the increase of the entropy of the system and the decrease of  $T_N$  [20]. Therefore, the  $T_N$  of undoped  $BiFeO_3$  is slightly lower than that of the  $BiFeO_3$  single crystal (643 K) [6].

It is well known that the magnet moment of  $Fe^{3+}$  arranges in a spatial modulating spiral structure. The superexchange interaction of Fe–O–Fe chain makes  $BiFeO_3$  an antiferromagnetic material [21]. Dipole polarity makes a main contribution to the dielectric constant of dielectric materials at low frequency ( $\leq 10^8$  Hz), and it is strongly related to the relative location between positive and negative charge center which can be affected by the length of Fe–O bond [22].

During the antiferromagnetism–paramagnetism transition, the rearrangement of  $Fe^{3+}$  magnetic moment will bring slight changes to the relative location between  $Fe^{3+}$  and  $O^{2-}$  due to the ferroelasticity of  $BiFeO_3$  [23]. As a result, the relative location of positive and negative charge center changes and then dielectric constant will be affected. Since the magnetic moment ordering and dielectric constant are strongly correlated by Fe–O bond, the observed abnormal dielectric constant near  $T_N$  could be an indirect evidence for magneto-electric coupling in BFZO.

Because the net magnet moment of  $Zr^{4+}$  is zero, the doped  $Zr^{4+}$  ions in BFZO will disturb the spatial modulating spiral structure of  $Fe^{3+}$  magnetic moment. The relative location of positive and negative charge centers will be affected by doping as well. As a result, the  $T_N$  and dielectric constant are affected by  $Zr^{4+}$  doping. Due to the doping antimagnetic  $Zr^{4+}$  ions, the spiral ordering of  $Fe^{3+}$  magnetic moment is disturbed and the magnetic entropy increases. So  $T_N$  of  $Zr^{4+}$  doped samples decreased  $\sim 20$  °C compared with that of the undoped  $BiFeO_3$  [20].

The magnetic properties of BFZO at room temperature are shown in Fig. 4. Almost all of the BFZO samples are antiferromagnetic according to the  $M-E$  plots. The doping amount of  $Zr^{4+}$  ions scarcely affects the magnetic type of BFZO samples although the  $T_N$  of  $Zr^{4+}$  doped  $BiFeO_3$  decreased.

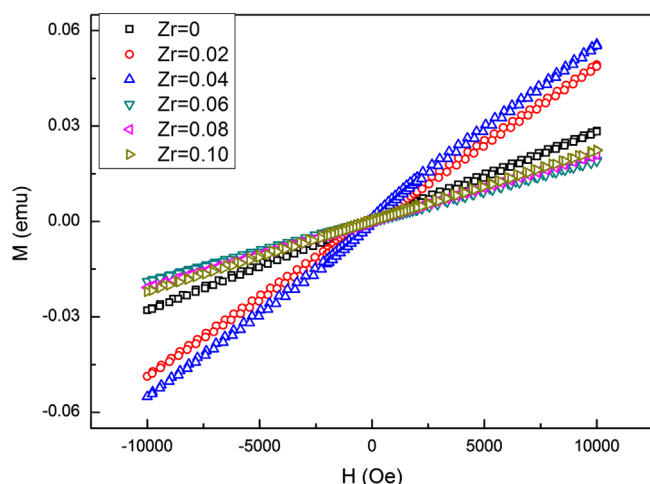


Fig. 4. The  $H$ – $M$  plots of BFZO at room temperature.

#### 4. Conclusions

Multiferroic  $\text{BiFe}_{1-x}\text{Zr}_x\text{O}_3$  (BFZO,  $x=0, 0.02, 0.04, 0.06, 0.08, 0.10$ ) samples were prepared by a solid state reaction method and characterized by XRD and XAFS. The analysis results reveal that the  $\text{Zr}^{4+}$  indeed entered into the crystal lattice of  $\text{BiFeO}_3$ , and  $\text{Zr}$ – $\text{O}$  bond is much shorter than  $\text{Fe}$ – $\text{O}$  bond. The magneto-electric coupling was indirectly observed in the dielectric constant–temperature spectra. The  $T_N$  of  $\text{Zr}^{4+}$  doped samples decreased  $\sim 20^\circ\text{C}$  comparing with that of the undoped  $\text{BiFeO}_3$ . All the as-prepared BFZO samples are antiferromagnetic.

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